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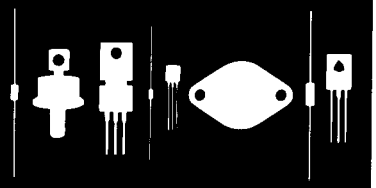
145 Adams Avenue
Hauppauge, New York 11788



D33D26

NPN SILICON TRANSISTOR

JEDEC TO-92 CASE (ECB)

DESCRIPTION

The CENTRAL SEMICONDUCTOR D33D26 type is an NPN silicon transistor manufactured by the epitaxial planar process, designed for general purpose, high current applications.

MAXIMUM RATINGS ($T_A = 25°C$)

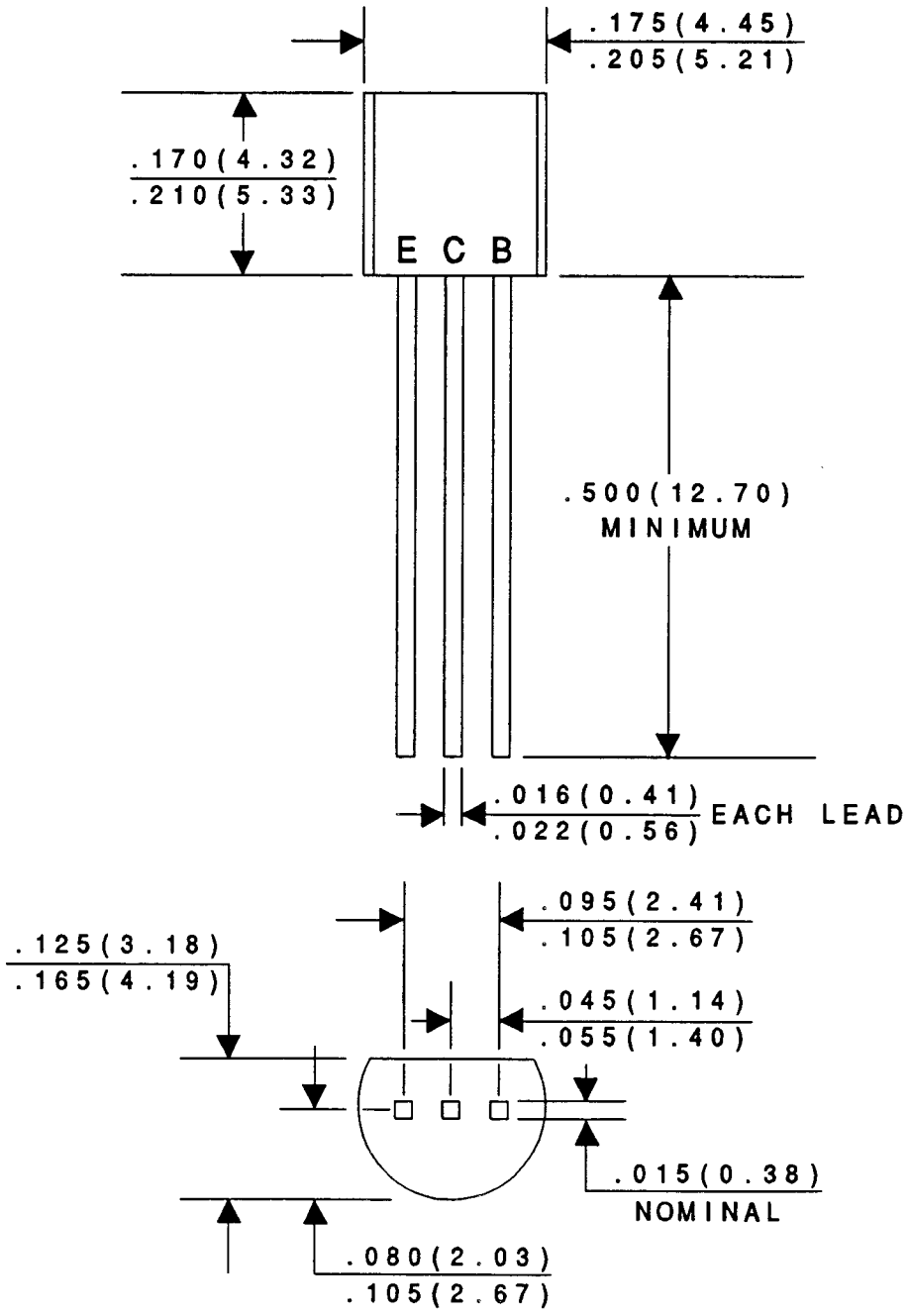
	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CES}	50	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	750	mA
Peak Collector Current	I_{CM}	1000	mA
Power Dissipation	P_D	625	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	200	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CES}	$V_{CE} = 25V$		100	nA
I_{CES}	$V_{CE} = 25V$, $T_A = 100°C$		15	μA
BV_{CES}	$I_C = 10\mu A$	50		V
BV_{CEO}	$I_C = 10mA$	40		V
BV_{EBO}	$I_E = 10\mu A$	5.0		V
$V_{CE(SAT)}$	$I_C = 500mA$, $I_B = 50mA$		0.75	V
$V_{BE(SAT)}$	$I_C = 500mA$, $I_B = 50mA$		1.2	V
h_{FE}	$V_{CE} = 2.0V$, $I_C = 2.0mA$	150	300	
h_{FE}	$V_{CE} = 2.0V$, $I_C = 500mA$	25		
C_{cb}	$V_{CB} = 10V$, $f = 1.0MHz$		15	pF
C_{eb}	$V_{EB} = 0.5V$, $f = 1.0MHz$		55	pF
f_T	$V_{CE} = 2.0V$, $I_C = 50mA$, $f = 20MHz$	135		MHz

(OVER)

JEDEC TO-92 - MECHANICAL DIMENSIONS



NOTE: ALL DIMENSIONS IN INCHES (mm).

Central™
Semiconductor Corp.

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824
www.centralsemi.com